

61090

**SURFACE MOUNT (NPN)
GENERAL PURPOSE TRANSISTOR
(2N2222AUB)**

Mii
OPTOELECTRONIC PRODUCTS
DIVISION

Features:

- Hermetically sealed
- Miniature package to minimize circuit board area
- Ceramic surface mount package
- Footprint and pin-out matches SOT-23 packaged transistors
- MIL-PRF-19500 screening available

Applications:

- Analog Switches
- Signal Conditioning
- Small Signal Amplifiers
- High Density Packaging

DESCRIPTION

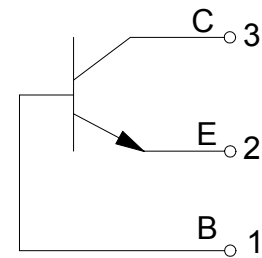
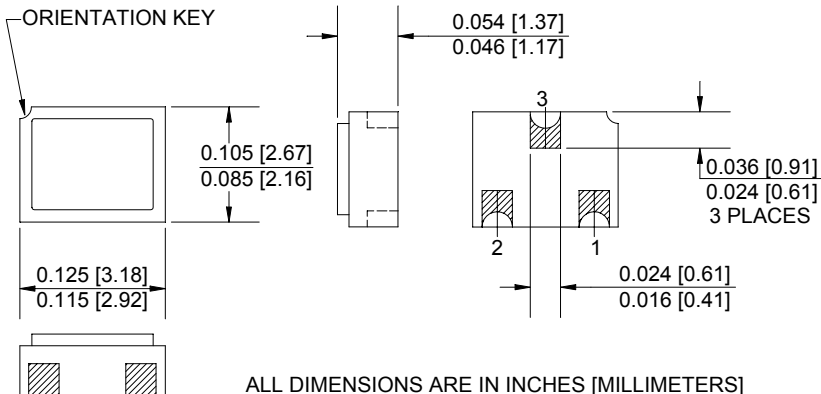
The **61090** is a hermetically sealed ceramic surface mount general purpose switching transistor. This miniature ceramic package is ideal for designs where board space and device weight are important requirements. This device is available custom binned to customer specifications or screened to MIL-PRF-19500.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	75V
Collector-Emitter Voltage	50V
Emitter-Collector Voltage	6V
Continuous Collector Current	800mA
Power Dissipation (Derate at the rate of 3.33 mW/°C above 25°C)	500mW
Maximum Junction Temperature	+200°C
Operating Temperature (See part selection guide for actual operating temperature)	-65°C to +200°C
Storage Temperature	-65°C to +200°C
Lead Soldering Temperature (vapor phase reflow for 30 seconds)	215°C

Package Dimensions

Schematic Diagram



ELECTRICAL CHARACTERISTICST_A = 25°C unless otherwise specified.

PARAMETER	SYMBOL	MIN	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	BV _{CBO}	75		V	I _C = 10μA, I _E = 0	
Collector-Emitter Breakdown Voltage	BV _{CEO}	50		V	I _C = 10mA, I _B = 0μA	
Emitter-Base Breakdown Voltage	BV _{EBO}	6		V	I _C = 0, I _E = 10μA	
Collector-Base Cutoff Current	I _{CBO}		10	nA	V _{CB} = 60V, I _E = 0	
			10	μA	V _{CB} = 60V, I _E = 0, T _A = 150°C	
Collector-Emitter Cutoff Current	I _{CES}		50	nA	V _{CE} = 50V	
Emitter-Base Cutoff Current	I _{EBO}		10	nA	V _{EB} = 4.0V, I _C = 0	
Forward-Current Transfer Ratio	h _{fe1}	50		-	V _{CE} = 10V, I _C = 0.1mA	
	h _{fe2}	75	325	-	V _{CE} = 10V, I _C = 1mA	
	h _{fe3}	100		-	V _{CE} = 10V, I _C = 10mA	
	h _{fe4}	100	300	-	V _{CE} = 10V, I _C = 150mA	1
	h _{fe5}	30		-	V _{CE} = 10V, I _C = 500mA	1
	h _{fe6}	35		-	V _{CE} = 10V, I _C = 10mA @ -55°C	
Collector-Emitter Saturation Voltage	V _{CE (SAT)}		0.30	V	I _C = 150mA, I _B = 15mA	1
			1.0	V	I _C = 500mA, I _B = 50mA	1
Base-Emitter Saturation Voltage	V _{BE (SAT)}	0.6	1.20	V	I _C = 150mA, I _B = 15mA	1
			2.0	V	I _C = 500mA, I _B = 50mA	1

SMALL-SIGNAL CHARACTERISTICS

Small Signal Forward Current Transfer Ratio	h _{fe}	50		-	V _{CE} = 10V, I _C = 1mA, f = 1kHz	
Small Signal Forward Current Transfer Ratio	h _{fe}	2.5		-	V _{CE} = 20V, I _C = 20mA, f = 100kHz	
Open Circuit Output Capacitance	C _{OBO}		8	pf	V _{CB} = 10V, 100kHz, ≤ f ≤ 1 MHz	
Input Capacitance (Output Open Capacitance)	C _{IBO}		25	pf	V _{EB} = 0.5 V, 100kHz, ≤ f ≤ 1 MHz	
Turn-On Time	t _{on}		35	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = 15mA	
Turn-Off Time	t _{off}		300	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = I _{B2} = 15mA	

NOTES:

- Pulse width ≤ 300μs, duty cycle ≤ 2.0%.

RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Bias Voltage-Collector/Emitter	I _C	10	150	mA
Collector-Emitter Voltage	V _{CE}	5	20	V

SELECTION GUIDE

PART NUMBER	PART DESCRIPTION
61090-001	2N2222AUB PNP transistor, commercial version
61090-002	2N2222AUB PNP transistor, JAN level screening
61090-101	2N2222AUB PNP transistor, JANTX level screening
61090-102	2N2222AUB PNP transistor, JANTXV level screening
61090-300	2N2222AUB PNP transistor, JANS level screening